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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	11000
Number of Logic Elements/Cells	44000
Total RAM Bits	1990656
Number of I/O	203
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	381-FBGA
Supplier Device Package	381-CABGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5um-45f-7bg381c

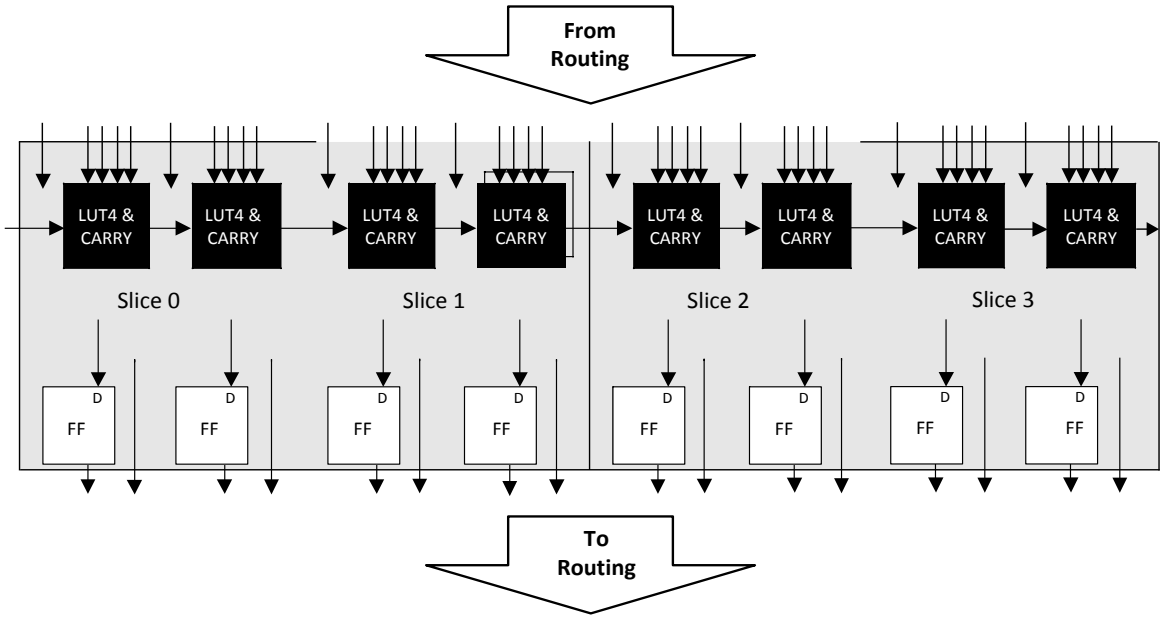


Figure 2.2. PFU Diagram

2.2.1. Slice

Each slice contains two LUT4s feeding two registers. In Distributed SRAM mode, Slice 0 through Slice 2 are configured as distributed memory, and Slice 3 is used as Logic or ROM. Table 2.1 shows the capability of the slices along with the operation modes they enable. In addition, each PFU contains logic that allows the LUTs to be combined to perform functions such as LUT5, LUT6, LUT7 and LUT8. There is control logic to perform set/reset functions (programmable as synchronous/ asynchronous), clock select, chip-select and wider RAM/ROM functions.

Table 2.1. Resources and Modes Available per Slice

Slice	PFU (Used in Distributed SRAM)		PFU (Not used as Distributed SRAM)	
	Resources	Modes	Resources	Modes
Slice 0	2 LUT4s and 2 Registers	RAM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 1	2 LUT4s and 2 Registers	RAM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 2	2 LUT4s and 2 Registers	RAM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 3	2 LUT4s and 2 Registers	Logic, Ripple, ROM	2 LUT4s and 2 Registers	Logic, Ripple, ROM

Figure 2.3 shows an overview of the internal logic of the slice. The registers in the slice can be configured for positive/negative and edge triggered or level sensitive clocks.

Each slice has 14 input signals, 13 signals from routing and one from the carry-chain (from the adjacent slice or PFU). There are five outputs, four to routing and one to carry-chain (to the adjacent PFU). There are two inter slice/ PFU output signals that are used to support wider LUT functions, such as LUT6, LUT7 and LUT8. Table 2.2 and Figure 2.3 list the signals associated with all the slices. Figure 2.4 on page 16 shows the connectivity of the inter-slice/PFU signals that support LUT5, LUT6, LUT7 and LUT8.

2.7. DDRDLL

Every DDRDLL (master DLL block) can generate phase shift code representing the amount of delay in a delay block that corresponding to 90° phase of the reference clock input. The reference clock can be either from PLL, or input pin. This code is used in the DQSBUF block that controls a set of DQS pin groups to interface with DDR memory (slave DLL). There are two DDRDLLs that supply two sets of codes (for two different reference clock frequencies) to each side of the I/Os (at each of the corners). The DQSBUF uses this code to controls the DQS input of the DDR memory to 90° shift to clock DQs at the center of the data eye for DDR memory interface.

The code is also sent to another slave DLL, DLLDEL, that takes a clock input and generates a 90° shift clock output to drive the clocking structure. This is useful to interface edge-aligned Generic DDR, where 90° clocking needs to be created. Figure 2.10 shows DDRDLL functional diagram.

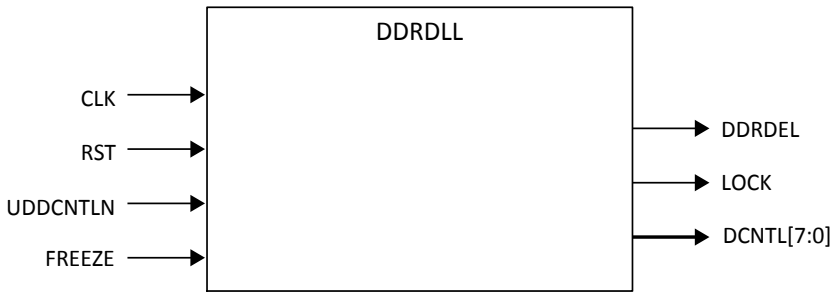


Figure 2.10. DDRDLL Functional Diagram

Table 2.5. DDRDLL Ports List

Port Name	Type	Description
CLK	Input	Reference clock input to the DDRDLL. Should run at the same frequency as the clock to the delay code.
RST	Input	Reset Input to the DDRDLL.
UDDCNTLN	Input	Update Control to update the delay code. The code is the DCNTL[7:0] outputs. These outputs are updated when the UDDCNTLN signal is LOW.
FREEZE	Input	FREEZE goes high and, without a glitch, turns off the DLL internal clock and the ring oscillator output clock. When FREEZE goes low, it turns them back on.
DDRDEL	Output	The delay codes from the DDRDLL to be used in DQSBUF or DLLDEL.
LOCK	Output	Lock output to indicate the DDRDLL has valid delay output.
DCNTL [7:0]	Output	The delay codes from the DDRDLL available for the user IP.

There are four identical DDRDLLs, one in each of the four corners in LFE5-85 and LFE5-45 devices, and two DDRDLLs in both LFE5-25 & LFE5-12 devices in the upper two corners. Each DDRDLL can generate delay code based on the reference frequency. The slave DLL (DQSBUF and DLLDEL) use the code to delay the signal, to create the phase shifted signal used for either DDR memory, to create 90° shift clock. Figure 2.11 shows the DDRDLL and the slave DLLs on the top level view.

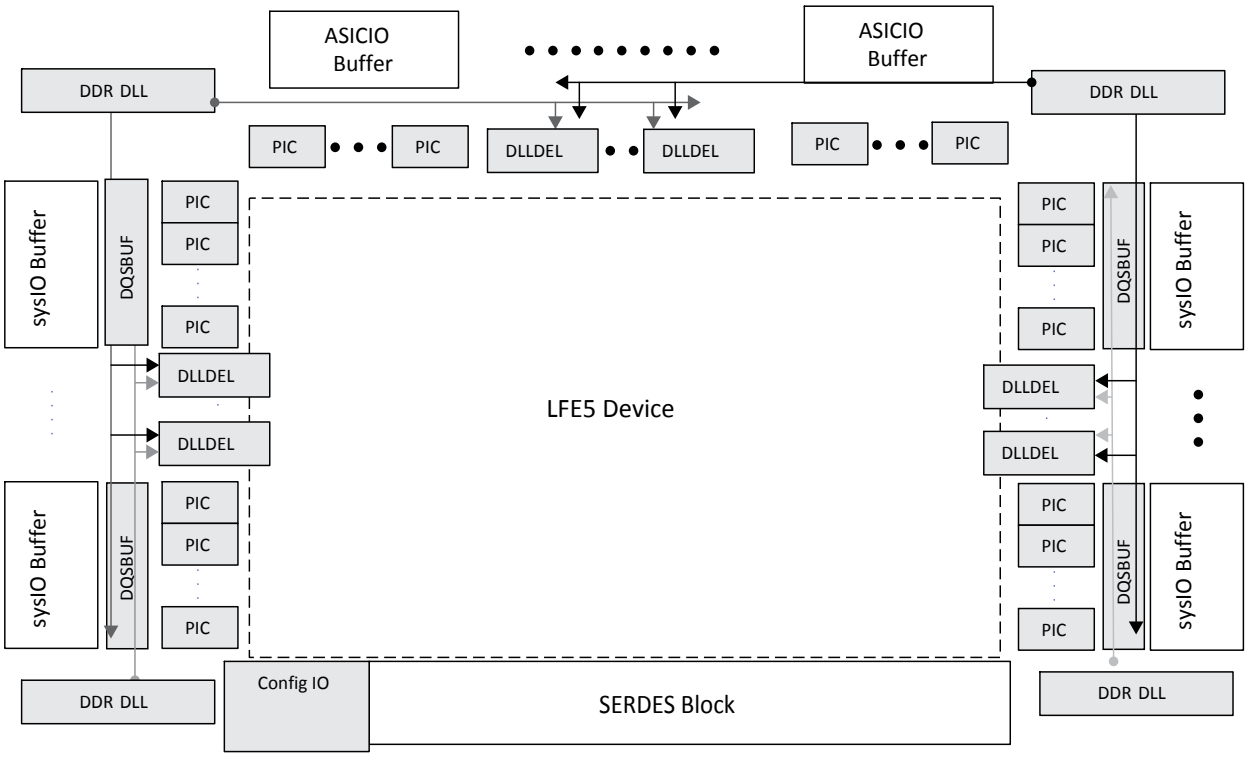


Figure 2.11. ECP5/ECP5-5G DLL Top Level View (For LFE-45 and LFE-85)

2.8. sysMEM Memory

ECP5/ECP5-5G devices contain a number of sysMEM Embedded Block RAM (EBR). The EBR consists of an 18 Kb RAM with memory core, dedicated input registers and output registers with separate clock and clock enable. Each EBR includes functionality to support true dual-port, pseudo dual-port, single-port RAM, ROM and FIFO buffers (via external PFUs).

2.8.1. sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as listed in Table 2.6 on page 25. FIFOs can be implemented in sysMEM EBR blocks by implementing support logic with PFUs. The EBR block facilitates parity checking by supporting an optional parity bit for each data byte. EBR blocks provide byte-enable support for configurations with 18-bit and 36-bit data widths. For more information, refer to ECP5 and ECP5-5G Memory Usage Guide (TN1264).

2.8.6. Memory Core Reset

The memory array in the EBR utilizes latches at the A and B output ports. These latches can be reset asynchronously or synchronously. RSTA and RSTB are local signals, which reset the output latches associated with Port A and Port B, respectively. The Global Reset (GSRN) signal can reset both ports. The output data latches and associated resets for both ports are as shown in Figure 2.12.

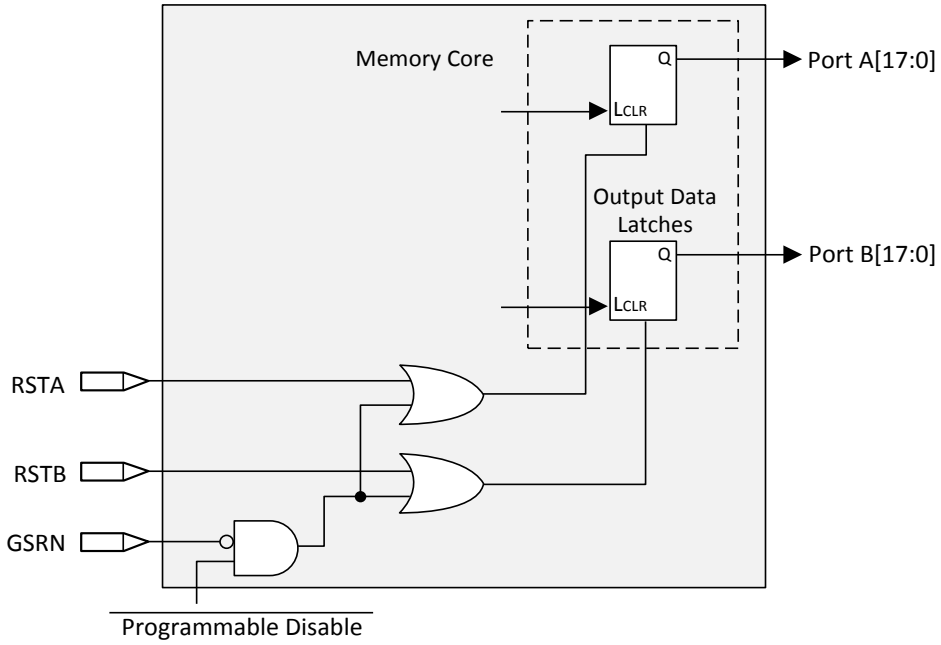


Figure 2.12. Memory Core Reset

For further information on the sysMEM EBR block, see the list of technical documentation in Supplemental Information section on page 102.

2.9. sysDSP™ Slice

The ECP5/ECP5-5G family provides an enhanced sysDSP architecture, making it ideally suited for low-cost, high-performance Digital Signal Processing (DSP) applications. Typical functions used in these applications are Finite Impulse Response (FIR) filters, Fast Fourier Transforms (FFT) functions, Correlators, Reed-Solomon/Turbo/Convolution encoders and decoders. These complex signal processing functions use similar building blocks such as multiply-adders and multiply-accumulators.

2.9.1. sysDSP Slice Approach Compared to General DSP

Conventional general-purpose DSP chips typically contain one to four (Multiply and Accumulate) MAC units with fixed data-width multipliers; this leads to limited parallelism and limited throughput. Their throughput is increased by higher clock speeds. In the ECP5/ECP5-5G device family, there are many DSP slices that can be used to support different data widths. This allows designers to use highly parallel implementations of DSP functions. Designers can optimize DSP performance vs. area by choosing appropriate levels of parallelism. Figure 2.13 compares the fully serial implementation to the mixed parallel and serial implementation.

In Figure 2.15, note that A_ALU, B_ALU and C_ALU are internal signals generated by combining bits from AA, AB, BA BB and C inputs. For further information, refer to ECP5 and ECP5-5G sysDSP Usage Guide (TN1267).

The ECP5/ECP5-5G sysDSP block supports the following basic elements.

- MULT (Multiply)
- MAC (Multiply, Accumulate)
- MULTADDSUB (Multiply, Addition/Subtraction)
- MULTADDSUBSUM (Multiply, Addition/Subtraction, Summation)

Table 2.7 shows the capabilities of each of the ECP5/ECP5-5G slices versus the above functions.

Table 2.7. Maximum Number of Elements in a Slice

Width of Multiply	x9	x18	x36
MULT	4	2	1/2
MAC	1	1	—
MULTADDSUB	2	1	—
MULTADDSUBSUM	1*	1/2	—

***Note**: One slice can implement 1/2 9x9 m9x9addsubsum and two m9x9addsubsum with two slices.

Some options are available in the four elements. The input register in all the elements can be directly loaded or can be loaded as a shift register from previous operand registers. By selecting “dynamic operation” the following operations are possible:

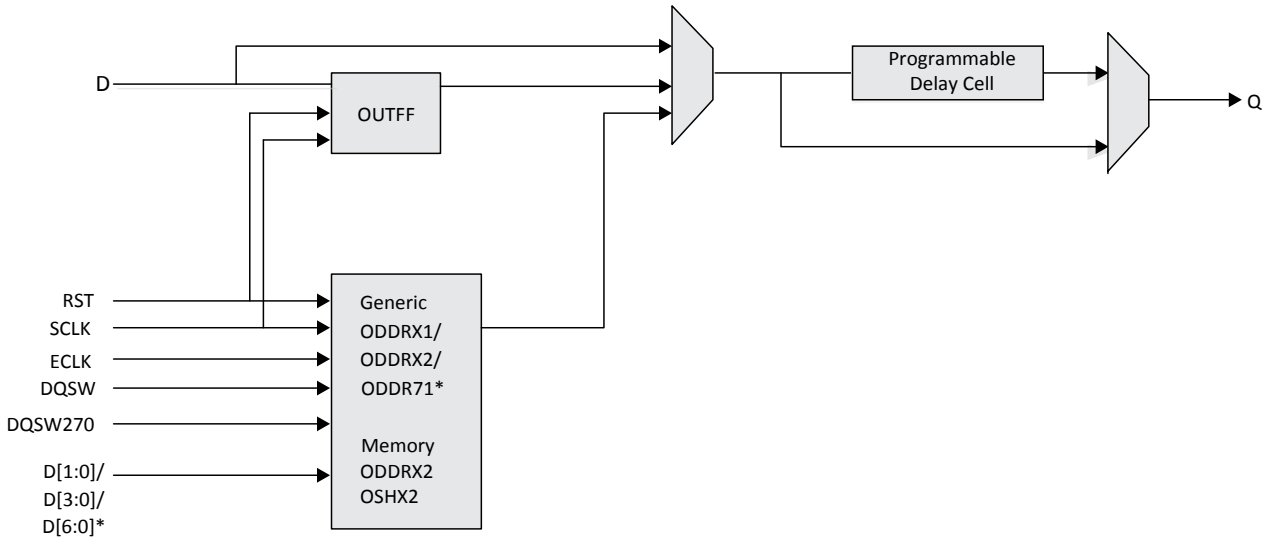
- In the Add/Sub option the Accumulator can be switched between addition and subtraction on every cycle.
- The loading of operands can switch between parallel and serial operations.

For further information, refer to ECP5 and ECP5-5G sysDSP Usage Guide (TN1267).

2.10. Programmable I/O Cells

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the ECP5/ECP5-5G devices, the Programmable I/O cells (PIC) are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the ECP5/ECP5-5G devices, two adjacent PIOs can be combined to provide a complementary output driver pair. All PIO pairs can implement differential receivers. Half of the PIO pairs on the left and right edges of these devices can be configured as true LVDS transmit pairs.



*For 7:1 LVDS interface only. It is required to use PIO pair pins PIOA/B.

Figure 2.20. Output Register Block on Left and Right Sides

Table 2.9. Output Block Port Description

Name	Type	Description
Q	Output	High Speed Data Output
D	Input	Data from core to output SDR register
D[1:0]/D[3:0]/ D[6:0]	Input	Low Speed Data from device core to output DDR register
RST	Input	Reset to the Output Block
SCLK	Input	Slow Speed System Clock
ECLK	Input	High Speed Edge Clock
DQSW	Input	Clock from DQS control Block used to generate DDR memory DQS output
DQSW270	Input	Clock from DQS control Block used to generate DDR memory DQ output

2.12. Tristate Register Block

The tristate register block registers tristate control signals from the core of the device before they are passed to the sysIO buffers. The block contains a register for SDR operation. In SDR, TD input feeds one of the flip-flops that then feeds the output. In DDR operation used mainly for DDR memory interface can be implemented on the left and right sides of the device. Here two inputs feed the tristate registers clocked by both ECLK and SCLK.

Figure 2.21 and Figure 2.22 show the Tristate Register Block functions on the device. For detailed description of the tristate register block modes and usage, refer to ECP5 and ECP5-5G High-Speed I/O Interface (TN1265).

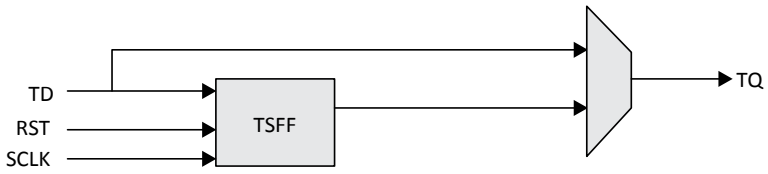


Figure 2.21. Tristate Register Block on Top Side

3.3. Power Supply Ramp Rates

Table 3.3. Power Supply Ramp Rates

Symbol	Parameter	Min	Typ	Max	Unit
t_{RAMP}	Power Supply ramp rates for all supplies	0.01	—	10	V/ms

Note: Assumes monotonic ramp rates.

3.4. Power-On-Reset Voltage Levels

Table 3.4. Power-On-Reset Voltage Levels

Symbol	Parameter			Min	Typ	Max	Unit
V_{PORUP}	All Devices	Power-On-Reset ramp-up trip point (Monitoring V_{CC}, V_{CCAUX}, and V_{CCIO8})	V_{CC}	0.90	—	1.00	V
			V_{CCAUX}	2.00	—	2.20	V
			V_{CCIO8}	0.95	—	1.06	V
V_{PORDN}	All Devices	Power-On-Reset ramp-down trip point (Monitoring V_{CC}, and V_{CCAUX}	V_{CC}	0.77	—	0.87	V
			V_{CCAUX}	1.80	—	2.00	V

Notes:

- These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
- Only V_{CCIO8} has a Power-On-Reset ramp up trip point. All other V_{CCIOs} do not have Power-On-Reset ramp up detection.
- V_{CCIO8} does not have a Power-On-Reset ramp down detection. V_{CCIO8} must remain within the Recommended Operating Conditions to ensure proper operation.

3.5. Power up Sequence

Power-On-Reset (POR) puts the ECP5/ECP5-5G device in a reset state. POR is released when V_{CC}, V_{CCAUX}, and V_{CCIO8} are ramped above the V_{PORUP} voltage, as specified above.

V_{CCIO8} controls the voltage on the configuration I/O pins. If the ECP5/ECP5-5G device is using Master SPI mode to download configuration data from external SPI Flash, it is required to ramp V_{CCIO8} above V_{IH} of the external SPI Flash, before at least one of the other two supplies (V_{CC} and/or V_{CCAUX}) is ramped to V_{PORUP} voltage level. If the system cannot meet this power up sequence requirement, and requires the V_{CCIO8} to be ramped last, then the system must keep either PROGRAMN or INITN pin LOW during power up, until V_{CCIO8} reaches V_{IH} of the external SPI Flash. This ensures the signals driven out on the configuration pins to the external SPI Flash meet the V_{IH} voltage requirement of the SPI Flash.

For LFE5UM/LFE5UM5G devices, it is required to power up V_{CCA}, before V_{CCAUXA} is powered up.

3.6. Hot Socketing Specifications

Table 3.5. Hot Socketing Specifications

Symbol	Parameter	Condition	Min	Typ	Max	Unit
IDK_HS	Input or I/O Leakage Current for Top and Bottom Banks Only	$0 \le V_{IN} \le V_{IH}$ (Max)	—	—	±1	mA
IDK	Input or I/O Leakage Current for Left and Right Banks Only	$0 \le V_{IN} < V_{CCIO}$	—	—	±1	mA
		$V_{CCIO} \le V_{IN} \le V_{CCIO} + 0.5$ V	—	18	—	mA

Notes:

1. V_{CC}, V_{CCAUX} and V_{CCIO} should rise/fall monotonically.
2. I_{DK} is additive to I_{PU}, I_{PW} or I_{BH}.
3. LVCMOS and LVTTL only.
4. Hot socket specification defines when the hot socketed device's junction temperature is at 85 °C or below. When the hot socketed device's junction temperature is above 85 °C, the I_{DK} current can exceed ±1 mA.

3.11. SERDES Power Supply Requirements[1,2,3]

Over recommended operating conditions.

Table 3.9. ECP5UM

Symbol	Description	Typ	Max	Unit
Standby (Power Down)				
I_{CCA-SB}	V_{CCA} Power Supply Current (Per Channel)	4	9.5	mA
$I_{CCHRX-SB}$[4]	V_{CCHRX}, Input Buffer Current (Per Channel)	—	0.1	mA
$I_{CCHTX-SB}$	V_{CCHTX}, Output Buffer Current (Per Channel)	—	0.9	mA
Operating (Data Rate = 3.125 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	43	54	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 2.5 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	40	50	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 1.25 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	34	43	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 270 Mb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	28	38	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	8	10	mA

Notes:

1. Rx Equalization enabled, Tx De-emphasis (pre-cursor and post-cursor) disabled
2. Per Channel current is calculated with both channels on in a Dual, and divide current by two. If only one channel is on, current will be higher.
3. To calculate with Tx De-emphasis enabled, use the Diamond Power Calculator tool.
4. For $I_{CCHRX-SB}$, during Standby, input termination on Rx are disabled.
5. For $I_{CCHRX-OP}$, during operational, the max specified when external AC coupling is used. If externally DC coupled, the power is based on current pulled down by external driver when the input is driven to LOW.

3.13. sysI/O Single-Ended DC Electrical Characteristics

Table 3.12. Single-Ended DC Characteristics

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max (V)	V_{OH} Min (V)	I_{OL}[1] (mA)	I_{OH}[1] (mA)
	Min (V)	Max (V)	Min (V)	Max (V)				
LVCMOS33	–0.3	0.8	2.0	3.465	0.4	V_{CCIO} – 0.4	16, 12, 8, 4	–16, –12, –8, –4
LVCMOS25	–0.3	0.7	1.7	3.465	0.4	V_{CCIO} – 0.4	12, 8, 4	–12, –8, –4
LVCMOS18	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.465	0.4	V_{CCIO} – 0.4	12, 8, 4	–12, –8, –4
LVCMOS15	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.465	0.4	V_{CCIO} – 0.4	8, 4	–8, –4
LVCMOS12	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.465	0.4	V_{CCIO} – 0.4	8, 4	–8, –4
LVTTL33	–0.3	0.8	2.0	3.465	0.4	V_{CCIO} – 0.4	16, 12, 8, 4	–16, –12, –8, –4
SSTL18_I (DDR2 Memory)	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	3.465	0.4	V_{CCIO} – 0.4	6.7	–6.7
SSTL18_II	–0.3	V_{REF} –	V_{REF} + 0.125	3.465	0.28	V_{CCIO} – 0.28	13.4	–13.4
SSTL15 _I (DDR3 Memory)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.465	0.31	V_{CCIO} – 0.31	7.5	–7.5
SSTL15_II (DDR3 Memory)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.465	0.31	V_{CCIO} – 0.31	8.8	–8.8
SSTL135_I (DDR3L Memory)	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	3.465	0.27	V_{CCIO} – 0.27	7	–7
SSTL135_II (DDR3L Memory)	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	3.465	0.27	V_{CCIO} – 0.27	8	–8
MIPI D-PHY (LP)[3]	–0.3	0.55	0.88	3.465	—	—	—	—
HSUL12 (LPDDR2/3 Memory)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.465	0.3	V_{CCIO} – 0.3	4	–4

Notes:

1. For electromigration, the average DC current drawn by the I/O pads within a bank of I/Os shall not exceed 10 mA per I/O (All I/Os used in the same V_{CCIO}).
2. Not all IO types are supported in all banks. Refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262) for details.
3. MIPI D-PHY LP input can be implemented by powering VCCIO to 1.5V, and select MIPI LP primitive to meet MIPI Alliance spec on V_{IH} and V_{IL}. It can also be implemented as LVCMOS12 with VCCIO at 1.2V, which would meet V_{IH}/V_{IL} spec on LVCOM12.

Table 3.20. Register-to-Register Performance

Function	–8 Timing	Unit
Basic Functions		
16-Bit Decoder	441	MHz
32-Bit Decoder	441	MHz
64-Bit Decoder	332	MHz
4:1 Mux	441	MHz
8:1 Mux	441	MHz
16:1 Mux	441	MHz
32:1 Mux	441	MHz
8-Bit Adder	441	MHz
16-Bit Adder	441	MHz
64-Bit Adder	441	MHz
16-Bit Counter	384	MHz
32-Bit Counter	317	MHz
64-Bit Counter	263	MHz
64-Bit Accumulator	288	MHz
Embedded Memory Functions		
1024x18 True-Dual Port RAM (Write Through or Normal), with EBR Output Registers	272	MHz
1024x18 True-Dual Port RAM (Read-Before-Write), with EBR Output Registers	214	MHz
Distributed Memory Functions		
16 x 2 Pseudo-Dual Port or 16 x 4 Single Port RAM (One PFU)	441	MHz
16 x 4 Pseudo-Dual Port (Two PFUs)	441	MHz
DSP Functions		
9 x 9 Multiplier (All Registers)	225	MHz
18 x 18 Multiplier (All Registers)	225	MHz
36 x 36 Multiplier (All Registers)	225	MHz
18 x 18 Multiply-Add/Sub (All Registers)	225	MHz
18 x 18 Multiply/Accumulate (Input and Output Registers)	225	MHz

Notes:

1. These functions were generated using Lattice Diamond design software tool. Exact performance may vary with the device and the design software tool version. The design software tool uses internal parameters that have been characterized but are not tested on every device.
2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from Lattice Diamond design software tool.

3.16. Derating Timing Tables

Logic timing provided in the following sections of this data sheet and the Diamond design tools are worst case numbers in the operating range. Actual delays at nominal temperature and voltage for best case process, can be much better than the values given in the tables. The Diamond design tool can provide logic timing numbers at a particular temperature and voltage.

Table 3.22. ECP5/ECP5-5G External Switching Characteristics *(Continued)*

Parameter	Description	Device	–8		–7		–6		Unit
			Min	Max	Min	Max	Min	Max	
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Data Input Delay	All Devices	0	—	0	—	0	—	ns
Generic DDR Input									
Generic DDRX1 Inputs With Clock and Data Centered at Pin (GDDRX1_RX.SCLK.Centered) Using PCLK Clock Input - Figure 3.6									
$t_{SU\_GDDRX1\_centered}$	Data Setup Before CLK Input	All Devices	0.52	—	0.52	—	0.52	—	ns
$t_{HD\_GDDRX1\_centered}$	Data Hold After CLK Input	All Devices	0.52	—	0.52	—	0.52	—	ns
$f_{DATA\_GDDRX1\_centered}$	GDDRX1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
$f_{MAX\_GDDRX1\_centered}$	GDDRX1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Inputs With Clock and Data Aligned at Pin (GDDRX1_RX.SCLK.Aligned) Using PCLK Clock Input - Figure 3.7									
$t_{SU\_GDDRX1\_aligned}$	Data Setup from CLK Input	All Devices	—	–0.55	—	–0.55	—	–0.55	ns + 1/2 UI
$t_{HD\_GDDRX1\_aligned}$	Data Hold from CLK Input	All Devices	0.55	—	0.55	—	0.55	—	ns + 1/2 UI
$f_{DATA\_GDDRX1\_aligned}$	GDDRX1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
$f_{MAX\_GDDRX1\_aligned}$	GDDRX1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX2 Inputs With Clock and Data Centered at Pin (GDDRX2_RX.ECLK.Centered) Using PCLK Clock Input, Left and Right sides Only - Figure 3.6									
$t_{SU\_GDDRX2\_centered}$	Data Setup before CLK Input	All Devices	0.321	—	0.403	—	0.471	—	ns
$t_{HD\_GDDRX2\_centered}$	Data Hold after CLK Input	All Devices	0.321	—	0.403	—	0.471	—	ns
$f_{DATA\_GDDRX2\_centered}$	GDDRX2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
$f_{MAX\_GDDRX2\_centered}$	GDDRX2 CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
Generic DDRX2 Inputs With Clock and Data Aligned at Pin (GDDRX2_RX.ECLK.Aligned) Using PCLK Clock Input, Left and Right sides Only - Figure 3.7									
$t_{SU\_GDDRX2\_aligned}$	Data Setup from CLK Input	All Devices	—	–0.344	—	–0.42	—	-0.495	ns + 1/2 UI
$t_{HD\_GDDRX2\_aligned}$	Data Hold from CLK Input	All Devices	0.344	—	0.42	—	0.495	—	ns + 1/2 UI
$f_{DATA\_GDDRX2\_aligned}$	GDDRX2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
$f_{MAX\_GDDRX2\_aligned}$	GDDRX2 CLK Frequency	All Devices	—	400	—	350	—	312	MHz
Video DDRX71 Inputs With Clock and Data Aligned at Pin (GDDRX71_RX.ECLK) Using PLL Clock Input, Left and Right sides Only Figure 3.11									
$t_{SU\_LVDS71\_i}$	Data Setup from CLK Input (bit i)	All Devices	—	–0.271	—	–0.39	—	–0.41	ns+(1/2+i) * UI
$t_{HD\_LVDS71\_i}$	Data Hold from CLK Input (bit i)	All Devices	0.271	—	0.39	—	0.41	—	ns+(1/2+i) * UI
f_{DATA_LVDS71}	DDR71 Data Rate	All Devices	—	756	—	620	—	525	Mb/s
f_{MAX_LVDS71}	DDR71 CLK Frequency (ECLK)	All Devices	—	378	—	310	—	262.5	MHz

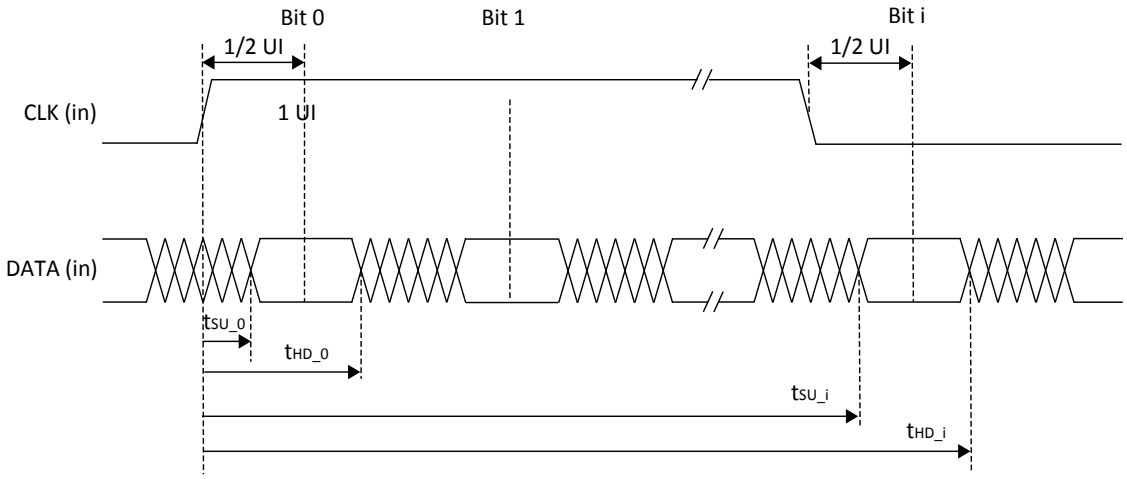


Figure 3.11. Receiver DDRX71_RX Waveforms

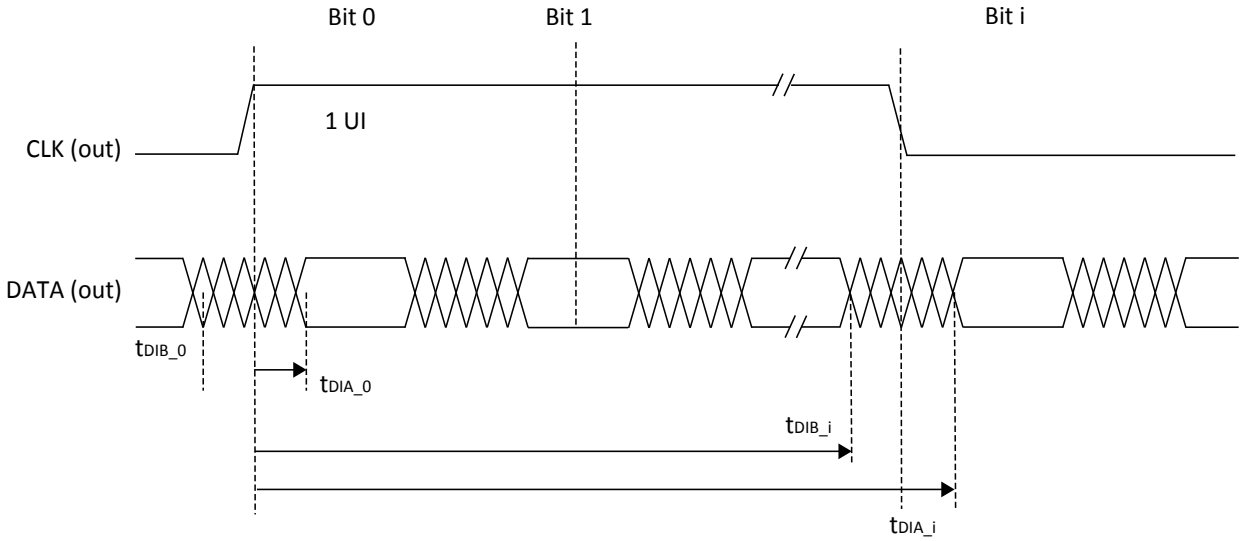
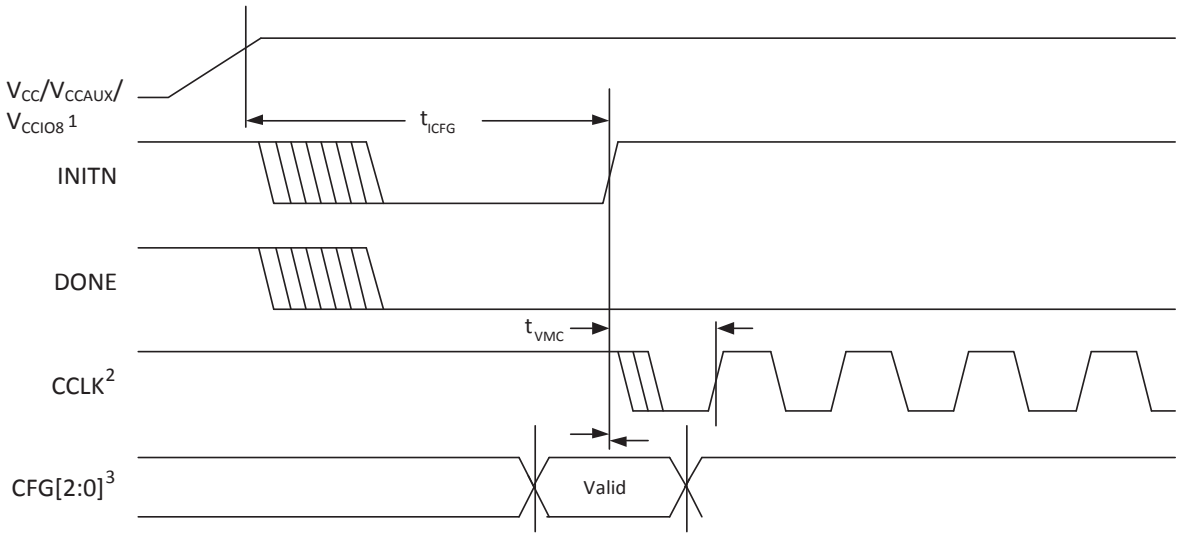


Figure 3.12. Transmitter DDRX71_TX Waveforms



1. Time taken from V_{CC}, V_{CCAUX} or V_{CCIO8}, whichever is the last to cross the POR trip point.
2. Device is in a Master Mode (SPI, SPIm).
3. The CFG pins are normally static (hardwired).

Figure 3.18. Power-On-Reset (POR) Timing

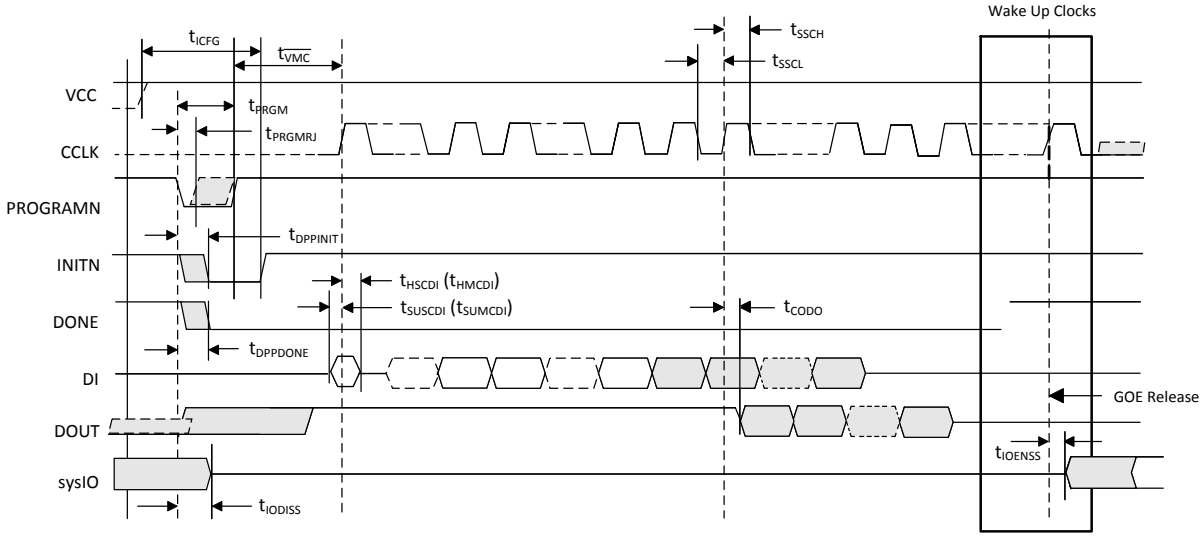


Figure 3.19. sysCONFIG Port Timing

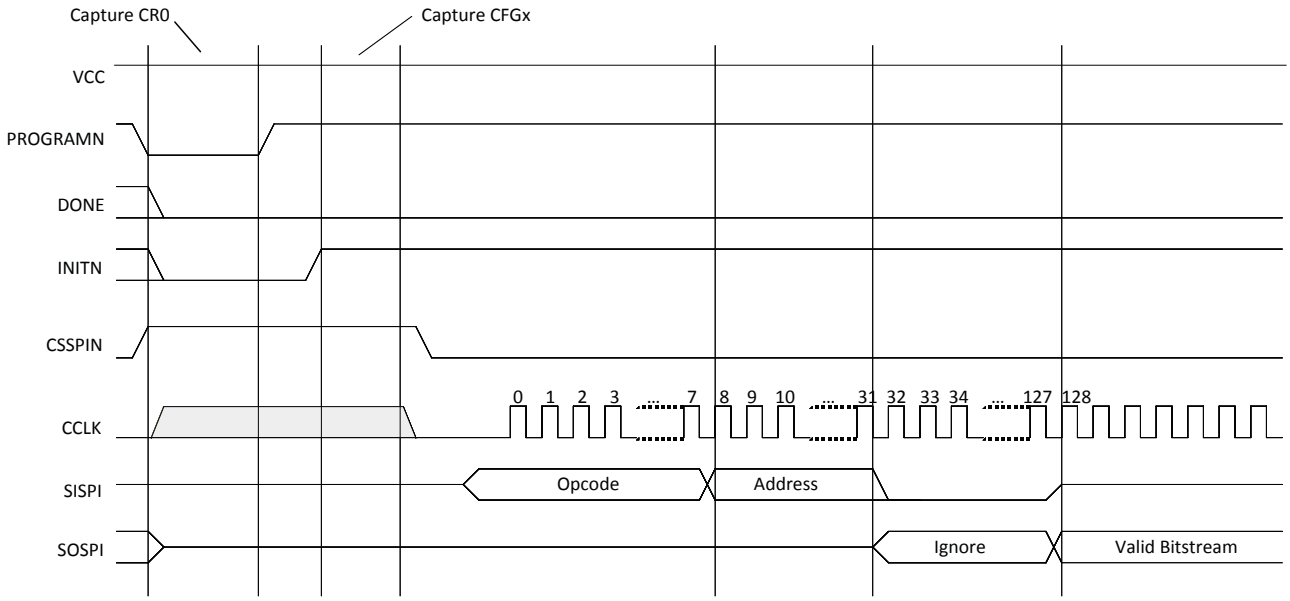


Figure 3.22. Master SPI Configuration Waveforms

3.32. JTAG Port Timing Specifications

Over recommended operating conditions.

Table 3.43. JTAG Port Timing Specifications

Symbol	Parameter	Min	Max	Units
f_{MAX}	TCK clock frequency	—	25	MHz
t_{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t_{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t_{BTS}	TCK [BSCAN] setup time	10	—	ns
t_{BTH}	TCK [BSCAN] hold time	8	—	ns
t_{BTRF}	TCK [BSCAN] rise/fall time	50	—	mV/ns
t_{BTCO}	TAP controller falling edge of clock to valid output	—	10	ns
$t_{BTCODIS}$	TAP controller falling edge of clock to valid disable	—	10	ns
t_{BTCOEN}	TAP controller falling edge of clock to valid enable	—	10	ns
t_{BTCRS}	BSCAN test capture register setup time	8	—	ns
t_{BTCRH}	BSCAN test capture register hold time	25	—	ns
t_{BUTCO}	BSCAN test update register, falling edge of clock to valid output	—	25	ns
$t_{BTUODIS}$	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
$t_{BTUPOEN}$	BSCAN test update register, falling edge of clock to valid enable	—	25	ns

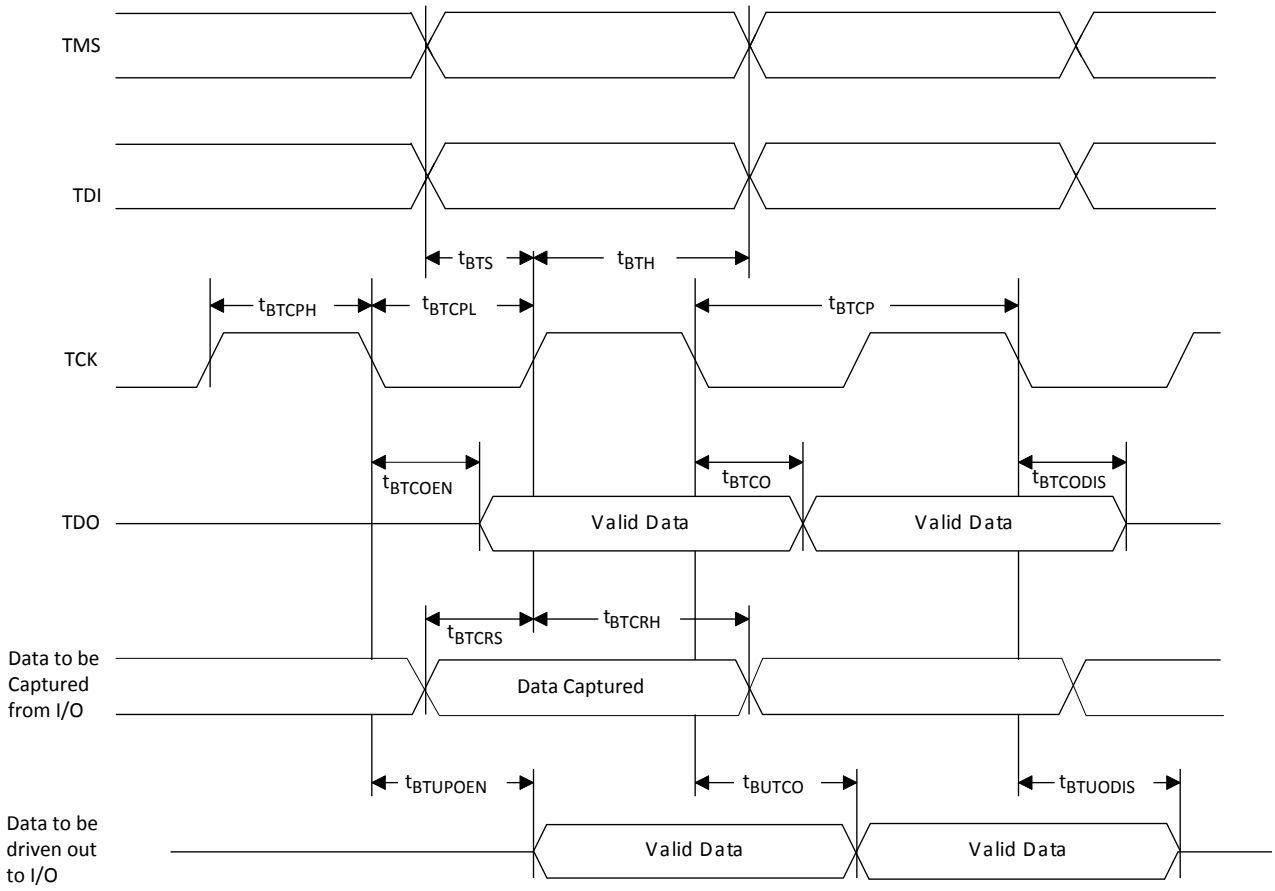
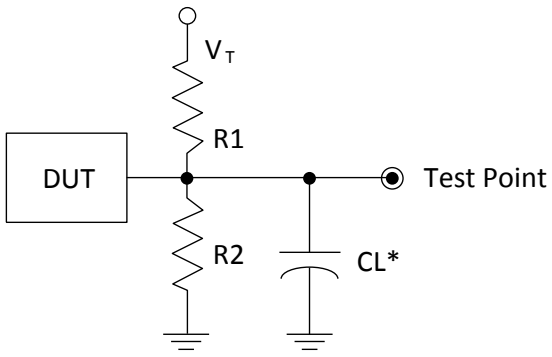


Figure 3.23. JTAG Port Timing Waveforms

3.33. Switching Test Conditions

Figure 3.24 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are listed in Table 3.44.



*CL Includes Test Fixture and Probe Capacitance

Figure 3.24. Output Test Load, LVTTL and LVCMOS Standards

4. Pinout Information

4.1. Signal Descriptions

Signal Name	I/O	Description
General Purpose		
P[L/R] [Group Number]_[A/B/C/D]	I/O	[L/R] indicates the L (Left), or R (Right) edge of the device. [Group Number] indicates the PIO [A/B/C/D] group. [A/B/C/D] indicates the PIO within the PIC to which the pad is connected. Some of these user-programmable pins are shared with special function pins. These pins, when not used as special purpose pins, can be programmed as I/Os for user logic. During configuration the user-programmable I/Os are tristated with an internal pull-down resistor enabled. If any pin is not used (or not bonded to a package pin), it is tristated and default to have pull-down enabled after configuration. PIO A and B are grouped as a pair, and PIO C and D are group as a pair. Each pair supports true LVDS differential input buffer. Only PIO A and B pair supports true LVDS differential output buffer. Each A/B and C/D pair supports programmable on/off differential input termination of 100 Ω.
P[T/B][Group Number]_[A/B]	I/O	[T/B] indicates the T (top) or B (bottom) edge of the device. [Group Number] indicates the PIO [A/B] group. [A/B] indicates the PIO within the PIC to which the pad is connected. Some of these user-programmable pins are shared with sysConfig pins. These pins, when not used as configuration pins, can be programmed as I/Os for user logic. During configuration, the pins not used in configuration are tristated with an internal pull-down resistor enabled. If any pin is not used (or not bonded to a package pin), it is tristated and default to have pull-down enabled after configuration. PIOs on top and bottom do not support differential input signaling or true LVDS output signaling, but it can support emulated differential output buffer. PIO A/B forms a pair of emulated differential output buffer.
GSRN	I	Global RESET signal (active low). Any I/O pin can be GSRN.
NC	—	No connect.
RESERVED	—	This pin is reserved and should not be connected to anything on the board.
GND	—	Ground. Dedicated pins.
V_{CC}	—	Power supply pins for core logic. Dedicated pins. V_{CC} = 1.1 V (ECP5), 1.2 V (ECP5UM5G)
V_{CCAUX}	—	Auxiliary power supply pin. This dedicated pin powers all the differential and referenced input buffers. V_{CCAUX} = 2.5 V.
V_{CCIOx}	—	Dedicated power supply pins for I/O bank x. V_{CCIO8} is used for configuration and JTAG.
VREF1_x	—	Reference supply pins for I/O bank x. Pre-determined shared pin in each bank are assigned as VREF1 input. When not used, they may be used as I/O pins.
PLL, DLL and Clock Functions		
[LOC][_GPLL[T, C]_IN	I	General Purpose PLL (GPLL) input pads: [LOC] = ULC, LLC, URC and LRC, T = true and C = complement. These pins are shared I/O pins. When not configured as GPLL input pads, they can be used as general purpose I/O pins.
GR_PCLK[Bank][num]	I	General Routing Signals in Banks 0, 1, 2, 3, 4, 6 and 7. There are two in each bank ([num] = 0, 1). Refer to ECP5 sysClock PLL/DLL Design and Usage Guide (TN1263). These pins are shared I/O pins. When not configured as GR pins, they can be used as general purpose I/O pins.
PCLK[T/C][Bank]_[num]	I/O	General Purpose Primary CLK pads: [T/C] = True/Complement, [Bank] = (0, 1, 2, 3, 6 and 7). There are two in each bank ([num] = 0, 1). These are shared I/ O pins. When not configured as PCLK pins, they can be used as general purpose I/O pins.

4.2. PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

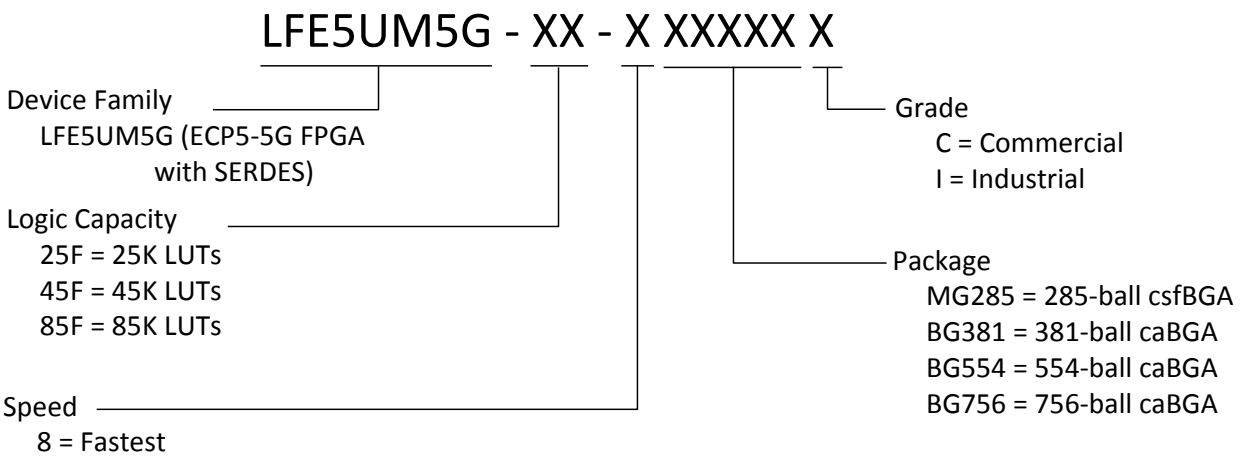
PICs Associated with DQS Strobe	PIO within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device Only		
P[L/R] [n–6]	A	DQ
	B	DQ
	C	DQ
	D	DQ
P[L/R] [n–3]	A	DQ
	B	DQ
	C	DQ
	D	DQ
P[L/R] [n]	A	DQS (P)
	B	DQS (N)
	C	DQ
	D	DQ
P[L/R] [n+3]	A	DQ
	B	DQ
	C	DQ
	D	DQ

Note: "n" is a row PIC number.

4.3. Pin Information Summary

4.3.1. LFE5UM/LFE5UM5G

Pin Information Summary		LFE5UM/ LFE5UM5G-25		LFE5UM/LFE5UM5G-45			LFE5UM/LFE5UM5G-85			
Pin Type		285 csfBG	381 caBGA	285 csfBGA	381 caBG	554 caBGA	285 csfBGA	381 caBG	554 caBGA	756 caBGA
General Purpose Inputs/Outputs per Bank	Bank 0	6	24	6	27	32	6	27	32	56
	Bank 1	6	32	6	33	40	6	33	40	48
	Bank 2	21	32	21	32	32	21	34	32	48
	Bank 3	28	32	28	33	48	28	33	48	64
	Bank 4	0	0	0	0	0	0	0	14	24
	Bank 6	26	32	26	33	48	26	33	48	64
	Bank 7	18	32	18	32	32	18	32	32	48
	Bank 8	13	13	13	13	13	13	13	13	13
Total Single-Ended User I/O		118	197	118	203	245	118	205	259	365
VCC		13	20	13	20	24	13	20	24	36
VCCAUX (Core)		3	4	3	4	9	3	4	9	8
VCCIO	Bank 0	1	2	1	2	3	1	2	3	4
	Bank 1	1	2	1	2	3	1	2	3	4
	Bank 2	2	3	2	3	4	2	3	4	4
	Bank 3	2	3	2	3	3	2	3	3	4
	Bank 4	0	0	0	0	0	0	0	2	2
	Bank 6	2	3	2	3	4	2	3	4	4
	Bank 7	2	3	2	3	3	2	3	3	4
	Bank 8	2	2	2	2	2	2	2	2	2



5.2. Ordering Part Numbers

5.2.1. Commercial

Part number	Grade	Package	Pins	Temp.	LUTs (K)	SERDES
LFE5U-12F-6BG256C	–6	Lead free caBGA	256	Commercial	12	No
LFE5U-12F-7BG256C	–7	Lead free caBGA	256	Commercial	12	No
LFE5U-12F-8BG256C	–8	Lead free caBGA	256	Commercial	12	No
LFE5U-12F-6MG285C	–6	Lead free csfBGA	285	Commercial	12	No
LFE5U-12F-7MG285C	–7	Lead free csfBGA	285	Commercial	12	No
LFE5U-12F-8MG285C	–8	Lead free csfBGA	285	Commercial	12	No
LFE5U-12F-6BG381C	–6	Lead free caBGA	381	Commercial	12	No
LFE5U-12F-7BG381C	–7	Lead free caBGA	381	Commercial	12	No
LFE5U-12F-8BG381C	–8	Lead free caBGA	381	Commercial	12	No
LFE5U-25F-6BG256C	–6	Lead free caBGA	256	Commercial	24	No
LFE5U-25F-7BG256C	–7	Lead free caBGA	256	Commercial	24	No
LFE5U-25F-8BG256C	–8	Lead free caBGA	256	Commercial	24	No
LFE5U-25F-6MG285C	–6	Lead free csfBGA	285	Commercial	24	No
LFE5U-25F-7MG285C	–7	Lead free csfBGA	285	Commercial	24	No
LFE5U-25F-8MG285C	–8	Lead free csfBGA	285	Commercial	24	No
LFE5U-25F-6BG381C	–6	Lead free caBGA	381	Commercial	24	No
LFE5U-25F-7BG381C	–7	Lead free caBGA	381	Commercial	24	No
LFE5U-25F-8BG381C	–8	Lead free caBGA	381	Commercial	24	No
LFE5U-45F-6BG256C	–6	Lead free caBGA	256	Commercial	44	No
LFE5U-45F-7BG256C	–7	Lead free caBGA	256	Commercial	44	No
LFE5U-45F-8BG256C	–8	Lead free caBGA	256	Commercial	44	No
LFE5U-45F-6MG285C	–6	Lead free csfBGA	285	Commercial	44	No
LFE5U-45F-7MG285C	–7	Lead free csfBGA	285	Commercial	44	No
LFE5U-45F-8MG285C	–8	Lead free csfBGA	285	Commercial	44	No
LFE5U-45F-6BG381C	–6	Lead free caBGA	381	Commercial	44	No
LFE5U-45F-7BG381C	–7	Lead free caBGA	381	Commercial	44	No
LFE5U-45F-8BG381C	–8	Lead free caBGA	381	Commercial	44	No
LFE5U-45F-6BG554C	–6	Lead free caBGA	554	Commercial	44	No
LFE5U-45F-7BG554C	–7	Lead free caBGA	554	Commercial	44	No

(Continued)

Date	Version	Section	Change Summary
August 2014	1.2	DC and Switching Characteristics	SERDES High-Speed Data Receiver section. Updated Table 3.26. Serial Input Data Specifications, Table 3.28. Receiver Total Jitter Tolerance Specification, and Table 3.29. External Reference Clock Specification (refclkp/refclkn).
			Modified section heading to XXAUI/CPRI LV E.30 Electrical and Timing Characteristics. Updated Table 3.33 Transmit and Table 3.34. Receive and Jitter Tolerance.
			Modified section heading to CPRI LV E.24 Electrical and Timing Characteristics. Updated Table 3.35. Transmit and Table 3.36. Receive and Jitter Tolerance.
			Modified section heading to Gigabit Ethernet/SGMII/CPRI LV E.12 Electrical and Timing Characteristics. Updated Table 3.37. Transmit and Table 3.38. Receive and Jitter Tolerance.
June 2014	1.1	Ordering Information	Updated ECP5/ECP5-5G Part Number Description and Ordering Part Numbers sections.
March 2014	1.0	All	Initial release.